

8050M (3DA8050M)

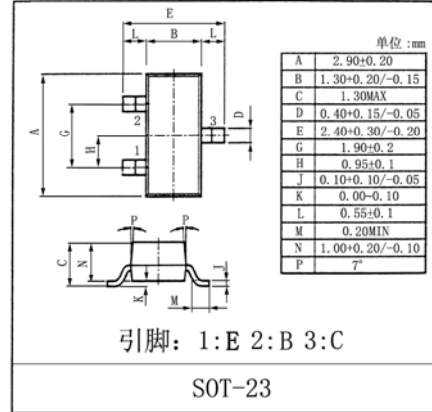
硅 NPN 半导体三极管/SILICON NPN TRANSISTOR

用途:用于功率放大电路。/Purpose: Power amplifier applications.

特点:与 8550M(3CA8550M) 互补。/Features: Complementary pair with 8550M(3CA8550M).

极限参数/Absolute maximum ratings(Ta=25°C)

参数符号 Symbol	数值 Rating	单位 Unit
V _{CBO}	40	V
V _{CEO}	25	V
V _{EBO}	6.0	V
I _C	1.5	A
I _B	0.5	A
P _C	625	mW
T _j	150	°C
T _{stg}	-55~150	°C



电性能参数/Electrical characteristics(Ta=25°C)

参数符号 Symbol	测试条件 Test condition	数值 Rating			单位 Unit
		最小值 Min	典型值 Typ	最大值 Max	
V _{CBO}	I _C =0.1mA I _E =0	40			V
V _{CEO}	I _C =2.0mA I _B =0	25			V
V _{EBO}	I _E =0.1mA I _C =0	6.0			V
I _{CBO}	V _{CB} =35V I _E =0			0.1	μA
I _{EBO}	V _{EB} =6.0V I _C =0			0.1	μA
h _{FE(1)}	V _{CE} =1.0V I _C =100mA	85		300	
h _{FE(2)}	V _{CE} =1.0V I _C =800mA	40			
h _{FE(3)}	V _{CE} =1.0V I _C =5.0mA	45			
V _{CE(sat)}	I _C =800mA I _B =80mA		0.28	0.5	V
V _{BE(sat)}	I _C =800mA I _B =80mA		0.98	1.2	V
V _{BE}	V _{CE} =1.0V I _C =10mA		0.66	1.0	V
f _T	V _{CE} =10V I _C =50mA	100	190		MHz
C _{ob}	V _{CB} =10V I _E =0 f=1.0MHz		9.0		pF

h_{FE(1)} 分档、印章/h_{FE(1)} Classifications、Marking:

h _{FE(1)} 分档 h _{FE(1)} Classifications	B	C	D
h _{FE(1)} 范围 h _{FE(1)} Range	85~160	120~200	160~300
印章 Marking	HY1B	HY1C	HY1D

